



KEY FEATURES



12BB Half-cut Cell Technology

New circuit design, lower internal current, lower Rs loss
Ga doped wafer, attenuation <2% (1st year) / ≤0.45% (Linear)



Industry Leading High Yield

Bifacial PERC cell technology,
5%-25% more yield depends on different conditions



Excellent Anti-PID Performance

2 times of industry standard Anti-PID test



ELECTRICAL CHARACTERISTICS

| Testing Condition | STC | NMOT |
|-------------------------------|-------|------|-------|------|-------|------|-------|------|-------|------|
| Maximum Power (Pmax/W) | | | | | | | | | | |
| Operating Voltage (Vmpp/V) | | | | | | | | | | |
| Operating Current (Impp/A) | | | | | | | | | | |
| Open-Circuit Voltage (Voc/V) | | | | | | | | | | |
| Short-Circuit Current (Isc/A) | | | | | | | | | | |
| Module Efficiency (%) | 20.70 | | 20.80 | | 21.00 | | 21.20 | | 21.40 | |

STC: Irradiance 1000W/m², Spectra at AM1.5, Module Temperature 25°C. Power output tolerance: 0~+5W, Test uncertainty for Pmax: ±3%

NMOT: Irradiance 800W/m², Spectra at AM1.5, Ambient Temperature 20°C, Wind speed 1m/s

REAR SIDE POWER GAIN(REFERENCE TO 595W FRONT)

| Pmax gain | 5% | 10% | 15% | 20% | 25% |
|-----------|-------|-------|-------|-------|-------|
| Pmax/W | 625 | 655 | 684 | 714 | 744 |
| Vmpp/V | 34.50 | 34.50 | 34.50 | 34.50 | 34.50 |
| Impp/A | 18.11 | 18.98 | 19.84 | 20.70 | 21.56 |
| Voc/V | 41.30 | 41.30 | 41.30 | 41.30 | 41.30 |
| Isc/A | 19.23 | 20.14 | 21.06 | 21.97 | 22.89 |